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(54) Title: METHOD OF MODIFYING A SUBSTRATE FOR DEPOSITION OF CHARGED PARTICLES THEREON

(57) Abstract: A method of modifying a substrate for deposition of charged particles thereon, the method comprising the steps of: providing a substrate that is incapable of bonding to a polyelectrolyte coating that has a charge that is opposite to the charge of the particles that are to be deposited thereon; modifying the surface of the substrate to provide a layer of silicon thereon or therein; and coating the silicon layered surface of the substrate with the polyelectrolyte coating, the polyelectrolyte coating containing functional groups that are capable of forming bonds with said silicon layer and wherein said polyelectrolyte coating enables a substantially even distribution of said charged particles to be deposited thereon.



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